

# Hiroki Hibino

## List of Publications by Citations

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223  
papers

5,926  
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37  
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g-index

246  
ext. papers

6,389  
ext. citations

4.5  
avg, IF

5.73  
L-index

#	Paper	IF	Citations
223	Single-walled carbon nanotube growth from highly activated metal nanoparticles. <i>Nano Letters</i> , <b>2006</b> , 6, 2642-5	11.5	389
222	Microscopic thickness determination of thin graphite films formed on SiC from quantized oscillation in reflectivity of low-energy electrons. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	301
221	Direct chemical vapor deposition growth of WS <sub>2</sub> atomic layers on hexagonal boron nitride. <i>ACS Nano</i> , <b>2014</b> , 8, 8273-7	16.7	234
220	Dependence of electronic properties of epitaxial few-layer graphene on the number of layers investigated by photoelectron emission microscopy. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	218
219	Carbon nanotube growth from semiconductor nanoparticles. <i>Nano Letters</i> , <b>2007</b> , 7, 2272-5	11.5	203
218	Domain Structure and Boundary in Single-Layer Graphene Grown on Cu(111) and Cu(100) Films. <i>Journal of Physical Chemistry Letters</i> , <b>2012</b> , 3, 219-226	6.4	186
217	Growth and Optical Properties of High-Quality Monolayer WS <sub>2</sub> on Graphite. <i>ACS Nano</i> , <b>2015</b> , 9, 4056-63	16.7	129
216	Quantum Faraday and Kerr rotations in graphene. <i>Nature Communications</i> , <b>2013</b> , 4, 1841	17.4	126
215	DC-Resistive-Heating-Induced Step Bunching on Vicinal Si (111). <i>Japanese Journal of Applied Physics</i> , <b>1990</b> , 29, L2254-L2256	1.4	121
214	Catalytic Growth of Graphene: Toward Large-Area Single-Crystalline Graphene. <i>Journal of Physical Chemistry Letters</i> , <b>2012</b> , 3, 2228-36	6.4	120
213	Mechanism of gold-catalyzed carbon material growth. <i>Nano Letters</i> , <b>2008</b> , 8, 832-5	11.5	102
212	Epitaxial few-layer graphene: towards single crystal growth. <i>Journal Physics D: Applied Physics</i> , <b>2010</b> , 43, 374005	3	96
211	Scalable synthesis of layer-controlled WS <sub>2</sub> and MoS <sub>2</sub> sheets by sulfurization of thin metal films. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 083112	3.4	94
210	Growth and low-energy electron microscopy characterization of monolayer hexagonal boron nitride on epitaxial cobalt. <i>Nano Research</i> , <b>2013</b> , 6, 335-347	10	93
209	Anisotropic layer-by-layer growth of graphene on vicinal SiC(0001) surfaces. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	93
208	Influence of Cu metal on the domain structure and carrier mobility in single-layer graphene. <i>Carbon</i> , <b>2012</b> , 50, 2189-2196	10.4	78
207	Carrier transport mechanism in graphene on SiC(0001). <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	77

206	Highly Uniform Bilayer Graphene on Epitaxial CuNi(111) Alloy. <i>Chemistry of Materials</i> , <b>2016</b> , 28, 4583-4592	3.3	75
205	Stacking domains of epitaxial few-layer graphene on SiC(0001). <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	74
204	High-temperature scanning-tunneling-microscopy observation of phase transitions and reconstruction on a vicinal Si(111) surface. <i>Physical Review B</i> , <b>1993</b> , 47, 13027-13030	3.3	70
203	Sublimation of the Si(111) surface in ultrahigh vacuum. <i>Physical Review B</i> , <b>1997</b> , 55, R10237-R10240	3.3	64
202	Theoretical Study of Epitaxial Graphene Growth on SiC(0001) Surfaces. <i>Applied Physics Express</i> , <b>2009</b> , 2, 065502	2.4	59
201	Half-Integer Quantum Hall Effect in Gate-Controlled Epitaxial Graphene Devices. <i>Applied Physics Express</i> , <b>2010</b> , 3, 075102	2.4	58
200	Decay kinetics of two-dimensional islands and holes on Si(111) studied by low-energy electron microscopy. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	55
199	Nonlinear terahertz field-induced carrier dynamics in photoexcited epitaxial monolayer graphene. <i>Physical Review B</i> , <b>2015</b> , 91,	3.3	53
198	Dynamics of the silicon (111) surface phase transition. <i>Nature</i> , <b>2000</b> , 405, 552-4	50.4	52
197	Growth Dynamics of Single-Layer Graphene on Epitaxial Cu Surfaces. <i>Chemistry of Materials</i> , <b>2015</b> , 27, 5377-5385	9.6	50
196	In situ scanning electron microscopy of graphene growth on polycrystalline Ni substrate. <i>Surface Science</i> , <b>2012</b> , 606, 728-732	1.8	49
195	Transient step bunching on a vicinal Si(111) surface. <i>Physical Review Letters</i> , <b>1994</b> , 72, 657-660	7.4	49
194	Hydrogen storage with titanium-functionalized graphene. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 013903	3.4	47
193	Characterization of doped single-wall carbon nanotubes by Raman spectroscopy. <i>Carbon</i> , <b>2011</b> , 49, 2264-2272	12.4	47
192	Fabrication and Integration of Nanostructures on Si Surfaces. <i>Accounts of Chemical Research</i> , <b>1999</b> , 32, 447-454	24.3	43
191	Surface-Mediated Aligned Growth of Monolayer MoS and In-Plane Heterostructures with Graphene on Sapphire. <i>ACS Nano</i> , <b>2018</b> , 12, 10032-10044	16.7	42
190	Atmospheric Pressure Chemical Vapor Deposition Growth of Millimeter-Scale Single-Crystalline Graphene on the Copper Surface with a Native Oxide Layer. <i>Chemistry of Materials</i> , <b>2016</b> , 28, 4893-4900	9.6	41
189	Thickness Determination of Graphene Layers Formed on SiC Using Low-Energy Electron Microscopy. <i>E-Journal of Surface Science and Nanotechnology</i> , <b>2008</b> , 6, 107-110	0.7	41

188	Plasmon transport in graphene investigated by time-resolved electrical measurements. <i>Nature Communications</i> , <b>2013</b> , 4, 1363	17.4	39
187	Growth of atomically thin hexagonal boron nitride films by diffusion through a metal film and precipitation. <i>Journal Physics D: Applied Physics</i> , <b>2012</b> , 45, 385304	3	37
186	Void growth during thermal decomposition of silicon oxide layers studied by low-energy electron microscopy. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 113519	2.5	37
185	On-chip graphene oxide aptasensor for multiple protein detection. <i>Analytica Chimica Acta</i> , <b>2015</b> , 866, 1-9	6.6	36
184	Resonant edge magnetoplasmons and their decay in graphene. <i>Physical Review Letters</i> , <b>2014</b> , 113, 2666014	14	36
183	Growth and electronic transport properties of epitaxial graphene on SiC. <i>Journal Physics D: Applied Physics</i> , <b>2012</b> , 45, 154008	3	36
182	Local conductance measurements of double-layer graphene on SiC substrate. <i>Nanotechnology</i> , <b>2009</b> , 20, 445704	3.4	36
181	Spatially Controlled Nucleation of Single-Crystal Graphene on Cu Assisted by Stacked Ni. <i>ACS Nano</i> , <b>2016</b> , 10, 11196-11204	16.7	35
180	Mesh pattern of Ge islands grown using solid phase epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1993</b> , 11, 2458-2462	2.9	34
179	Shot noise generated by graphene p-n junctions in the quantum Hall effect regime. <i>Nature Communications</i> , <b>2015</b> , 6, 8068	17.4	32
178	Step arrangement design and nanostructure self-organization on Si surfaces. <i>Applied Surface Science</i> , <b>1997</b> , 117-118, 642-651	6.7	32
177	Sublimation of a heavily boron-doped Si(111) surface. <i>Physical Review B</i> , <b>1998</b> , 58, 13146-13150	3.3	32
176	Vertical GaP nanowires arranged at atomic steps on Si(111) substrates. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 033114	3.4	31
175	Patterning-Assisted Control for Ordered Arrangement of Atomic Steps on Si(111) Surfaces. <i>Japanese Journal of Applied Physics</i> , <b>1995</b> , 34, L668-L670	1.4	29
174	Electrical Characterization of Bilayer Graphene Formed by Hydrogen Intercalation of Monolayer Graphene on SiC(0001). <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 02BN02	1.4	29
173	Site-controlled InP nanowires grown on patterned Si substrates. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 24, 133-137	3	28
172	Twinned epitaxial layers formed on Si(111)BB-B. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1998</b> , 16, 1934-1937	2.9	28
171	Molecular design for enhanced sensitivity of a FRET aptasensor built on the graphene oxide surface. <i>Chemical Communications</i> , <b>2013</b> , 49, 10346-8	5.8	27

170	Lattice-oriented catalytic growth of graphene nanoribbons on heteroepitaxial nickel films. <i>ACS Nano</i> , <b>2013</b> , 7, 10825-33	16.7	27
169	Protein recognition on a single graphene oxide surface fixed on a solid support. <i>Journal of Materials Chemistry B</i> , <b>2013</b> , 1, 1119-1124	7.3	26
168	Behavior and role of superficial oxygen in Cu for the growth of large single-crystalline graphene. <i>Applied Surface Science</i> , <b>2017</b> , 408, 142-149	6.7	25
167	Fabrication of nanostructures on silicon surfaces on wafer scale by controlling self-organization processes. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1996</b> , 14, 4134		25
166	Ultrathin Chemical Vapor Deposition (CVD)-Grown Hexagonal Boron Nitride as a High-Quality Dielectric for Tunneling Devices on Rigid and Flexible Substrates. <i>Journal of Physical Chemistry C</i> , <b>2014</b> , 118, 3340-3346	3.8	23
165	Chemical vapor deposition of boron- and nitrogen-containing graphene thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2012</b> , 177, 233-238	3.1	23
164	Impact of graphene quantum capacitance on transport spectroscopy. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	23
163	Quantum Hall Effect and Carrier Scattering in Quasi-Free-Standing Monolayer Graphene. <i>Applied Physics Express</i> , <b>2012</b> , 5, 125101	2.4	23
162	Reflection High-Energy Electron Diffraction Studies of Vicinal Si(111) Surfaces. <i>Japanese Journal of Applied Physics</i> , <b>1991</b> , 30, 1337-1342	1.4	23
161	Graphene FRET Aptasensor. <i>ACS Sensors</i> , <b>2016</b> , 1, 710-716	9.2	23
160	Graphene nanoribbon field-effect transistors fabricated by etchant-free transfer from Au(788). <i>Applied Physics Letters</i> , <b>2018</b> , 112, 021602	3.4	22
159	Graphene-modified interdigitated array electrode: fabrication, characterization, and electrochemical immunoassay application. <i>Analytical Sciences</i> , <b>2013</b> , 29, 55-60	1.7	22
158	Thin Graphitic Structure Formation on Various Substrates by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 04DH13	1.4	22
157	Phase transitions on Si(113): A high-temperature scanning-tunneling-microscopy study. <i>Physical Review B</i> , <b>1997</b> , 56, 4092-4097	3.3	22
156	Arrangement of AuBi alloy islands at atomic steps. <i>Surface Science</i> , <b>2005</b> , 588, L233-L238	1.8	22
155	Hysteresis in the (1 $\bar{1}$ )-(7 $\bar{7}$ ) first-order phase transition on the Si(111) surface. <i>Surface Science</i> , <b>2001</b> , 487, 191-200	1.8	22
154	Study of Graphene Growth by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol: Influence of Gas Flow Rate on Graphitic Material Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 06GE12 <sup>1-4</sup>	1.4	22
153	Structural Instability of Transferred Graphene Grown by Chemical Vapor Deposition against Heating. <i>Journal of Physical Chemistry C</i> , <b>2013</b> , 117, 22123-22130	3.8	21

152	Graphene-Based Nano-Electro-Mechanical Switch with High On/Off Ratio. <i>Applied Physics Express</i> , <b>2013</b> , 6, 055101	2.4	21
151	The physics of epitaxial graphene on SiC(0001). <i>Journal of Physics Condensed Matter</i> , <b>2012</b> , 24, 314215	1.8	21
150	Nonlinear transmission of an intense terahertz field through monolayer graphene. <i>AIP Advances</i> , <b>2014</b> , 4, 117118	1.5	20
149	In-plane conductance measurement of graphene nanoislands using an integrated nanogap probe. <i>Nanotechnology</i> , <b>2008</b> , 19, 495701	3.4	20
148	Step wandering induced by homoepitaxy on Si() during $\sqrt{3}\times\sqrt{3}$ phase transition. <i>Surface Science</i> , <b>2003</b> , 527, L222-L228	1.8	20
147	Reducing domain boundaries of surface reconstruction during molecular beam epitaxy on Si(111). <i>Applied Physics Letters</i> , <b>1995</b> , 67, 915-917	3.4	20
146	Raman spectroscopic investigation of polycrystalline structures of CVD-grown graphene by isotope labeling. <i>Nanoscale</i> , <b>2014</b> , 6, 13838-44	7.7	18
145	Correlation between morphology and transport properties of quasi-free-standing monolayer graphene. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 221604	3.4	18
144	Macroscopic Single-Domain Graphene Growth on Polycrystalline Nickel Surface. <i>Applied Physics Express</i> , <b>2012</b> , 5, 035501	2.4	18
143	Characterization of Optical Absorption and Polarization Dependence of Single-Layer Graphene Integrated on a Silicon Wire Waveguide. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 060203	1.4	18
142	Two-dimensional emission patterns of secondary electrons from graphene layers formed on SiC(0001). <i>Applied Surface Science</i> , <b>2008</b> , 254, 7596-7599	6.7	18
141	Step arrangement design and nanostructure self-organization on Si(111) surfaces by patterning-assisted control. <i>Applied Surface Science</i> , <b>1996</b> , 107, 1-5	6.7	18
140	Real-Time Observation of $(1\sqrt{3})\times(1\sqrt{3})$ Phase Transition on Vicinal Si(111) Surfaces by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>1993</b> , 32, 3247-3251	1.4	18
139	Step band structures on vicinal Si(111) surfaces created by DC resistive heating. <i>Applied Surface Science</i> , <b>1992</b> , 60-61, 479-484	6.7	18
138	Isothermal Growth and Stacking Evolution in Highly Uniform Bernal-Stacked Bilayer Graphene. <i>ACS Nano</i> , <b>2020</b> , 14, 6834-6844	16.7	17
137	Growth and low-energy electron microscopy characterizations of graphene and hexagonal boron nitride. <i>Progress in Crystal Growth and Characterization of Materials</i> , <b>2016</b> , 62, 155-176	3.5	17
136	Self-spreading of Supported Lipid Bilayer on SiO <sub>2</sub> Surface Bearing Graphene Oxide. <i>Chemistry Letters</i> , <b>2012</b> , 41, 1259-1261	1.7	17
135	Contact Conductance Measurement of Locally Suspended Graphene on SiC. <i>Applied Physics Express</i> , <b>2010</b> , 3, 045101	2.4	17

134	Design of Si surfaces for self-assembled nanoarchitecture. <i>Surface Science</i> , <b>2002</b> , 514, 1-9	1.8	17
133	Real-space observation of (111) facet formation on vicinal Si(111) surfaces. <i>Physical Review B</i> , <b>1995</b> , 51, 7753-7761	3.3	17
132	Pb preadsorption facilitates island formation during Ge growth on Si(111). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1994</b> , 12, 23-28	2.9	17
131	Surface structural changes during the initial growth of Ge on Si(111)7 × 7. <i>Applied Surface Science</i> , <b>1992</b> , 60-61, 112-119	6.7	17
130	Effects of hydrogen intercalation on transport properties of quasi-free-standing monolayer graphene. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 04EN01	1.4	16
129	Graphene Growth from a Spin-Coated Polymer without a Reactive Gas. <i>Applied Physics Express</i> , <b>2011</b> , 4, 065102	2.4	16
128	Step wandering due to the gap in diffusion coefficient on the upper and the lower terraces. <i>Surface Science</i> , <b>2003</b> , 522, 64-74	1.8	16
127	Orientation-controlled growth of hexagonal boron nitride monolayers templated from graphene edges. <i>Applied Physics Express</i> , <b>2017</b> , 10, 055102	2.4	15
126	Boron nitride growth on metal foil using solid sources. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2013</b> , 31, 041804	1.3	15
125	Stability and reactivity of steps in the initial stage of graphene growth on the SiC(0001) surface. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	15
124	Electrical Characterization of Bilayer Graphene Formed by Hydrogen Intercalation of Monolayer Graphene on SiC(0001). <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 02BN02	1.4	15
123	Disordering of Si(111) at high temperatures. <i>Physical Review B</i> , <b>1998</b> , 58, 12587-12589	3.3	15
122	Kinetics and Thermodynamics of Surface Steps on Semiconductors. <i>Critical Reviews in Solid State and Materials Sciences</i> , <b>1999</b> , 24, 227-263	10.1	15
121	On-chip FRET Graphene Oxide Aptasensor: Quantitative Evaluation of Enhanced Sensitivity by Aptamer with a Double-stranded DNA Spacer. <i>Analytical Sciences</i> , <b>2015</b> , 31, 875-9	1.7	14
120	Influence of graphene on quality factor variation in a silicon ring resonator. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 091122	3.4	14
119	Selective charge doping of chemical vapor deposition-grown graphene by interface modification. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 253116	3.4	14
118	Tuning of quantum interference in top-gated graphene on SiC. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	14
117	Diffusion barrier caused by 1 × 1 and 7 × 7 on Si(111) during phase transition. <i>Physical Review B</i> , <b>2001</b> , 64,	3.3	14



116	Catalyst-Selective Growth of Single-Orientation Hexagonal Boron Nitride toward High-Performance Atomically Thin Electric Barriers. <i>Advanced Materials</i> , <b>2019</b> , 31, e1900880	24	13
115	Site-Selective Epitaxy of Graphene on Si Wafers. <i>Proceedings of the IEEE</i> , <b>2013</b> , 101, 1557-1566	14.3	13
114	Photocurrent generation of a single-gate graphene p-n junction fabricated by interfacial modification. <i>Nanotechnology</i> , <b>2015</b> , 26, 385203	3.4	13
113	Chemical Vapor Deposition of Hexagonal Boron Nitride. <i>E-Journal of Surface Science and Nanotechnology</i> , <b>2012</b> , 10, 133-138	0.7	13
112	Observation of Band Gap in Epitaxial Bilayer Graphene Field Effect Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 04DN04	1.4	13
111	Formation of twinned two-bilayer-high islands during initial stages of Si growth on Si(111)-B. <i>Surface Science</i> , <b>1998</b> , 412-413, 132-140	1.8	13
110	Exchanges between group-III (B, Al, Ga, In) and Si atoms on Si(111)-sqrt(3) x sqrt(3) surfaces. <i>Physical Review B</i> , <b>1996</b> , 54, 5763-5768	3.3	13
109	Probing the extended-state width of disorder-broadened Landau levels in epitaxial graphene. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	12
108	Graphene Layer Formation on Polycrystalline Nickel Grown by Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 035103	1.4	12
107	Molecular beam epitaxial growth of graphene and ridge-structure networks of graphene. <i>Journal Physics D: Applied Physics</i> , <b>2011</b> , 44, 435305	3	12
106	Instability of steps during Ga deposition on Si(1 1 1). <i>Surface Science</i> , <b>2008</b> , 602, 2421-2426	1.8	12
105	Boron Nitride Thin Films Grown on Graphitized 6HSiC Substrates by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 2554-2557	1.4	12
104	Growth of Si twinning superlattice. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2001</b> , 87, 214-221	3.1	12
103	Enhanced terrace stability for preparation of step-free Si(001)-(2 x 1) surfaces. <i>Physical Review Letters</i> , <b>2001</b> , 87, 136103	7.4	12
102	Atomic and electronic structure of Si dangling bonds in quasi-free-standing monolayer graphene. <i>Nano Research</i> , <b>2018</b> , 11, 864-873	10	12
101	Core-level photoelectron spectroscopy study of interface structure of hydrogen-intercalated graphene on n-type 4H-SiC(0001). <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	11
100	Effects of environmental conditions on the ultrafast carrier dynamics in graphene revealed by terahertz spectroscopy. <i>Physical Review B</i> , <b>2017</b> , 95,	3.3	11
99	Epitaxial Trilayer Graphene Mechanical Resonators Obtained by Electrochemical Etching Combined with Hydrogen Intercalation. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CH01	1.4	11



98	Epitaxial Graphene Growth Studied by Low-Energy Electron Microscopy and First-Principles. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 597-602	0.4	11
97	Substitution of In for Si adatoms and exchanges between In and Si adatoms on a Si(111)-7 $\times$ 7 surface. <i>Physical Review B</i> , <b>1997</b> , 55, 7018-7022	3.3	11
96	Molecular beam epitaxial growth of graphene using cracked ethylene [Advantage over ethanol in growth. <i>Diamond and Related Materials</i> , <b>2013</b> , 34, 84-88	3.5	10
95	In situ scanning electron microscopy of graphene nucleation during segregation of carbon on polycrystalline Ni substrate. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 455301	3	10
94	Etchant-free and damageless transfer of monolayer and bilayer graphene grown on SiC. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 115101	1.4	10
93	Exchanges between Si and Pb adatoms on Si(111). <i>Surface Science</i> , <b>1995</b> , 328, L547-L552	1.8	10
92	Real-time scanning tunneling microscopy of phase transition and faceting on a vicinal Si(111) surface. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1993</b> , 11, 1640-1643	2.9	10
91	Trace of interface reconstruction in Ge solid-phase epitaxy on Si(111). <i>Physical Review B</i> , <b>1994</b> , 49, 5765-5768	3.5	10
90	Atomic Structure and Physical Properties of Epitaxial Graphene Islands Embedded in SiC(0001) Surfaces. <i>Applied Physics Express</i> , <b>2010</b> , 3, 115103	2.4	9
89	Direct evidence for Ge preferential growth at steps and out-of-phase boundaries of (7 $\times$ 7) domains on Si(111) in solid phase epitaxy. <i>Surface Science</i> , <b>1995</b> , 324, L333-L336	1.8	9
88	(7 $\times$ 7) to (7 $\times$ 7) phase transition on Si(111) under heating current. <i>Surface Science</i> , <b>1996</b> , 364, L587-L590	1.8	9
87	Two-stage phase transition of 12 x 1 reconstruction on Si(331). <i>Physical Review B</i> , <b>1996</b> , 53, 15682-15687	3.3	9
86	A Lattice Model for Thermal Decoration and Step Bunching in Vicinal Surface with Sub-Monolayer Adsorbates. <i>E-Journal of Surface Science and Nanotechnology</i> , <b>2009</b> , 7, 39-44	0.7	9
85	Quantum Hall effect in epitaxial graphene with permanent magnets. <i>Scientific Reports</i> , <b>2016</b> , 6, 38393	4.9	9
84	Ultra-fine metal gate operated graphene optical intensity modulator. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 251101	3.4	9
83	Etchant-free graphene transfer using facile intercalation of alkanethiol self-assembled molecules at graphene/metal interfaces. <i>Nanoscale</i> , <b>2016</b> , 8, 11503-10	7.7	9
82	Plasmon transport and its guiding in graphene. <i>New Journal of Physics</i> , <b>2014</b> , 16, 063055	2.9	8
81	Energy dissipation in edged and edgeless graphene mechanical resonators. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 064304	2.5	8

80	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 070115	1.4	8
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78	Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111). <i>Applied Surface Science</i> , <b>1994</b> , 82-83, 374-379	6.7	8
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